

AMENDMENTS TO THE CLAIMS:

Please amend the claims as follows:

1. (Currently amended) A semiconductor laser device comprising:
a substrate having a plurality of recessed portions in its principal surface, and
a plurality of semiconductor laser chips each disposed in one of the recessed portions,
wherein the semiconductor laser chips are a facet-emitting type in which a laser beam is
emitted from a facet,
plan configurations of the semiconductor laser chips and the recessed portions are
asymmetrical,
the recessed portions are formed so that the respective emission directions of the
semiconductor laser chips are aligned with each other and are substantially parallel to each other
with a distance therebetween, and
a notch, through which a laser-emitting portion of an associated one of the semiconductor
laser chips is exposed, is formed ~~[[in]]~~ at an edge portion of the substrate to face the laser-
emitting portion.

2-7. (Cancelled)

8. (Previously presented) A semiconductor laser device comprising:
a substrate having a plurality of recessed portions in its principal surface, and
a plurality of semiconductor laser chips each disposed in one of the recessed portions,
wherein the semiconductor laser chips are a facet-emitting type in which a laser beam is
emitted from a facet,

in each said semiconductor laser chip, optical output from its front facet is equal to optical output from its rear facet,

the recessed portions are formed so that the respective emission directions of the semiconductor laser chips are aligned with each other, and

a notch, through which a laser-emitting portion of an associated one of the semiconductor laser chips is exposed, is formed in the substrate to face the laser-emitting portion.

9-10. (Cancelled)

11. (Currently amended) ~~The device of Claim 1,~~ A semiconductor laser device comprising:

a substrate having a plurality of recessed portions in its principal surface, and
a plurality of semiconductor laser chips each disposed in one of the recessed portions,
wherein the semiconductor laser chips are a facet-emitting type in which a laser beam is emitted from a facet,

plan configurations of the semiconductor laser chips and the recessed portions are asymmetrical,

the recessed portions are formed so that the respective emission directions of the semiconductor laser chips are aligned with each other and are substantially parallel to each other with a distance therebetween, and

a notch, through which a laser-emitting portion of an associated one of the semiconductor laser chips is exposed, is formed in the substrate to face the laser-emitting portion, and

wherein the plan configurations of the semiconductor laser chips vary in accordance with their emission wavelengths.

12. (Currently amended) ~~The device of Claim 1,~~ A semiconductor laser device comprising:

a substrate having a plurality of recessed portions in its principal surface, and
a plurality of semiconductor laser chips each disposed in one of the recessed portions,
wherein the semiconductor laser chips are a facet-emitting type in which a laser beam is
emitted from a facet,

plan configurations of the semiconductor laser chips and the recessed portions are
asymmetrical,

the recessed portions are formed so that the respective emission directions of the
semiconductor laser chips are aligned with each other and are substantially parallel to each other
with a distance therebetween, and

a notch, through which a laser-emitting portion of an associated one of the semiconductor
laser chips is exposed, is formed in the substrate to face the laser-emitting portion, and

~~wherein~~ the semiconductor laser chips vary in shape in accordance with their optical outputs.

13. (Cancelled)

14. (Previously presented) A semiconductor laser device comprising:

a substrate having a plurality of recessed portions in its principal surface, and
a plurality of semiconductor laser chips each disposed in one of the recessed portions,
wherein a chip electrode is formed on a face of each said semiconductor laser chip which
faces the bottom face of the associated one of the recessed portions,

the recess electrode is formed such that an end portion of the recess electrode extends beyond the principal surface of the substrate and so as to be shared by the semiconductor laser chips, and

a notch, through which a laser-emitting portion of an associated one of the semiconductor laser chips is exposed, is formed in the substrate to face the laser-emitting portion.

15. (Withdrawn) A method for fabricating a semiconductor laser device, comprising the steps of:

(a) forming a plurality of recessed portions in the principal surface of a substrate, and
(b) spreading a plurality of semiconductor laser elements in the form of chips in a liquid and pouring the semiconductor-laser-element-spread liquid over the principal surface of the substrate, thereby allowing the semiconductor laser elements to be disposed into the respective recessed portions in a self-aligned manner,

wherein the semiconductor laser elements are a facet-emitting type in which a laser beam is emitted from a facet, and

in the step (a), the recessed portions are formed so that the respective emission directions of the semiconductor laser elements are aligned with each other.

16. (Withdrawn) The method of Claim 15, wherein the step (a) includes the step of forming in the substrate a notch through which a laser-emitting portion of an associated one of the semiconductor laser elements is exposed.

17. (Withdrawn) The method of Claim 15, wherein in the step (a), the recessed portions are so formed as to vary in plan configuration in accordance with the shapes of the associated semiconductor laser elements.

18. (New) The device of Claim 1, wherein the notch is formed in the substrate on front and rear facets of the semiconductor laser chips.

19. (New) The device of Claim 1, wherein the recessed portions and the notch have a same depth.